



SOT-89 Plastic-Encapsulate Transistors

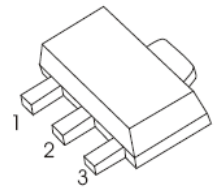
TRANSISTOR (PNP)

FEATURES

- NPN Complement to BC868
- Low Voltage
- High Current
- **Pb-Free package is available**
RoHS product for packing code suffix "G"
Halogen free product for packing code suffix "H"

SOT-89

1. BASE
2. COLLECTOR
3. EMITTER



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-32	V
V _{CEO}	Collector-Emitter Voltage	-20	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current	-1	A
P _C	Collector Power Dissipation	500	mW
R _{θJA}	Thermal Resistance From Junction To Ambient	250	°C/W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	-32			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-20			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-100μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-25V, I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-0.1	μA
DC current gain	h _{FE(1)}	V _{CE} =-10V, I _C =-5mA	50			
	h _{FE(2)}	V _{CE} =-1V, I _C =-0.5A	100		375	
	h _{FE(3)}	V _{CE} =-1V, I _C =-1A	60			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-1A, I _B =-0.1A			-0.5	V
Base -emitter voltage	V _{BE}	V _{CE} =-1V, I _C =-1A			-1	V
		V _{CE} =-10V, I _C =-5mA		-0.62		V
Transition frequency	f _T	V _{CE} =-5V, I _C =-10mA, f=100MHz	40			MHz

CLASSIFICATION OF h_{FE(2)}

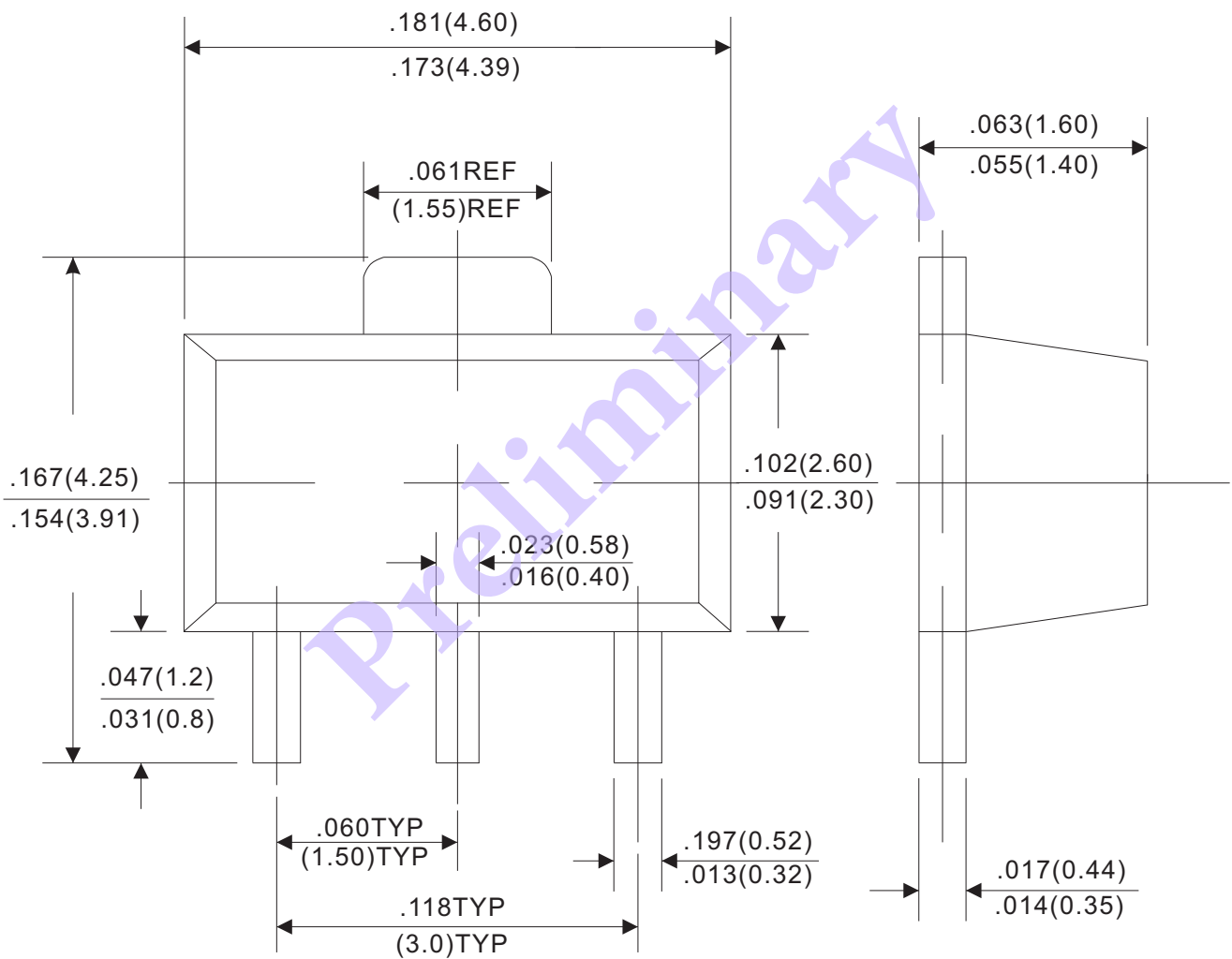
RANK	BC869	BC869-16	BC869-25
RANGE	100 - 375	100 - 250	160 - 375
MARKING	CEC	CGC	CHC



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Outline Drawing

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Dimensions in inches and (millimeters)

Rev.C